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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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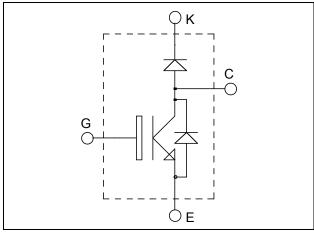


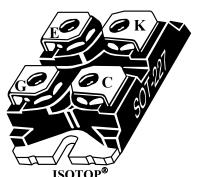


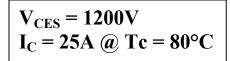




ISOTOP® Boost chopper Trench + Field Stop fast IGBT4 Power module







Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- Trench + Field Stop Fast IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Low leakage current
 - RBSOA and SCSOA rated

• Boost SiC Schottky Diode

- Zero reverse recovery
- Zero forward recovery
- Temperature Independent switching behavior
- Positive temperature coefficient on VF
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Low conduction losses
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings @ $T_i = 25$ °C unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
T	Continuous Collector Current	$T_C = 25^{\circ}C$	45	
I_{C}	Continuous Conector Current	$T_C = 80$ °C	25	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	50	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	170	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	50A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.7	2.05	2.4	V
	Conector Emitter saturation voltage	$I_C = 25A$	$T_{j} = 150^{\circ}C$		2.6		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 0.8 \text{mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				400	nA

Dynamic Characteristics

·	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			1430		
Coes	Output Capacitance	$V_{CE} = 25V$			115		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			85		
Q_{G}	Gate charge	$V_{GE} = \pm 15V$; $V_{CE} = 600V$ $I_{C} = 25A$			0.2		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		130		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			20		
$T_{d(off)}$	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 25A$ $R_{G} = 20\Omega$			300		ns
$T_{\rm f}$	Fall Time				45		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 25A$			150		ns
T_{r}	Rise Time				35		
$T_{d(off)}$	Turn-off Delay Time				350		
T_{f}	Fall Time	$R_G = 20\Omega$			80		
Eon	Turn-on Switching Energy	, GE =15 ,	$T_J = 25^{\circ}C$		1.2		mJ
Lon			$T_J = 150$ °C		1.8		1113
E_{off}	Turn-off Switching Energy	$I_C = 25A$ $R_G = 20\Omega$	$T_J = 25^{\circ}C$		1.5		mJ
Loff	Turn-off Switching Energy		$T_{\rm J} = 150^{\circ}{\rm C}$		2.2	2.2	
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bus} = 900V$ $t_p \le 10 \mu s ; T_j = 150 ^{\circ} C$			100		A

Chopper SiC diode ratings and characteristics

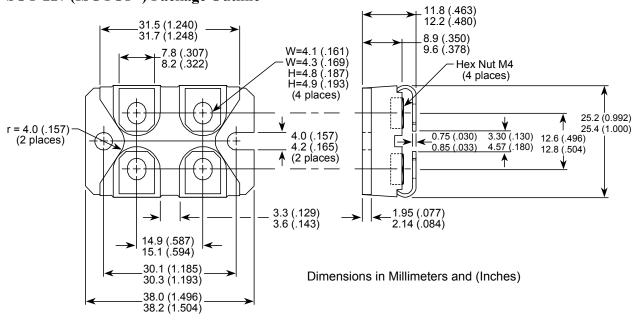
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
T	Maximum Reverse Leakage Current	$V_{p}=1200V_{p}$	$T_j = 25^{\circ}C$		70	500	^
I_{RM}			$T_j = 175$ °C		200	700	μA
I_F	DC Forward Current		Tc = 125°C		15		A
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm p} = 15\Delta$	$T_i = 25^{\circ}C$		1.5	1.8	V
v _F			$T_i = 175$ °C		2.2	3	V
Qc	Total Capacitive Charge	$I_F = 15A, V_R = 600V$ di/dt = 400A/\mus			100		nC
С	Total Capacitance	$f = 1 MHz, V_R = 400 V$			74		рF
	Total Capacitance	$f = 1 MHz, V_R =$	800V		54		þг



Thermal and package characteristics

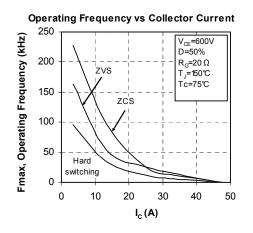
Symbol	Characteristic		Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance	IGBT			0.9	
R_{thJC}		SiC Diode			1.1	°C/W
R_{thJA}	Junction to Ambient (IGBT & Diode)				20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		2500			V
T_{J}, T_{STG}	Storage Temperature Range		-55		175	°C
$T_{ m L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	C
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

SOT-227 (ISOTOP®) Package Outline

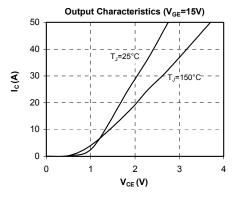


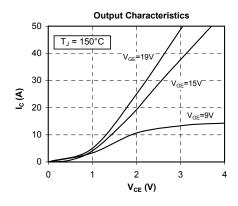
ISOTOP® is a registered trademark of ST Microelectronics NV

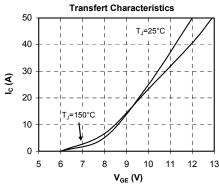
Typical Performance Curve

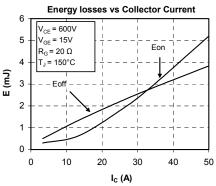


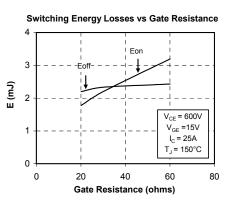


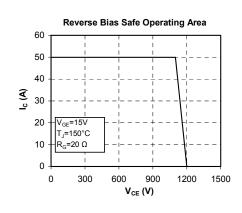


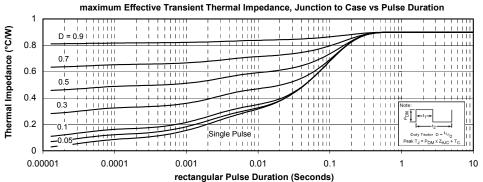












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